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Substitute for Form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Complete If Known	
				Application Number	W/803,445
				Filing Date	03/18/04
				First Named Inventor	Udayakumar et al.
				Group Art Unit	2811
Examiner Name	H. Ju				
Sheet	1	of	2	Attorney Docket No.	TI-36447

U.S. PATENT DOCUMENTS						
Exam. Initials*	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Doc.	Date of Pub. of Cited Doc. (mm-dd-yyyy)	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)			
✓	AA	5,452,178		Emesh et al.	09/19/1995	Entire Document
	AB	5,972,722		Visokay et al.	10/26/1999	Entire Document
	AC	6,090,697		Xing et al.	07/18/2000	Entire Document
	AD	6,144,060		Park et al.	11/07/2000	Entire Document
	AE	6,177,351	B1	Beratan et al.	01/23/2001	Entire Document
	AF	6,225,656	B1	Cuchiaro et al.	05/01/2001	Entire Document
	AG	6,242,299	B1	Hickert	06/05/2001	Entire Document
	AH	6,261,967	B1	Athavale et al.	07/17/2001	Entire Document
	AI	6,291,251	B1	Nam	09/18/2001	Entire Document
	AJ	2001/0034106	A1	Moise et al.	10/25/2001	Entire Document
	AK	2001/0044205	A1	Gilbert et al.	11/22/2001	Entire Document
	AL	6,355,952	B1	Yamoto et al.	03/12/2002	Entire Document
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	AN	6,423,592	B1	Sun	07/23/2002	Entire Document
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	AP	2003/0006439	A1	Bailey	01/09/2003	Entire Document
	AQ	6,512,256	B1	Cuchiaro et al.	01/28/2003	Entire Document
	AR	6,528,386	B1	Summerfelt et al.	03/04/2003	Entire Document
	AS	6,534,809	B2	Moise et al.	03/18/2003	Entire Document
	AT	2003/0098497	A1	Solayappan et al.	05/29/2003	Entire Document
	AU	6,576,482	B1	Aggarwal et al.	06/10/2003	Entire Document
	AV	6,576,942	B2	Okutoh et al.	06/10/2003	Entire Document
	AW	2003/0129847	A1	Celij et al.	07/10/2003	Entire Document
	AX	6,610,549	B1	Aggarwal et al.	08/26/2003	Entire Document
	AY	6,611,014	B1	Kanaya et al.	08/26/2003	Entire Document
✓	AZ	6,682,995	B2	Zhang et al.	01/27/2004	Entire Document

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Exam. Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
✓	CA	"FeRAM Tutorial", ALI SHEIKHOESLAMI and P. GLENN GULAK, A survey of circuit innovations in Ferroelectric random-access memories, Proceedings of the IEEE, Vol. 88, No. 3, May, 2000, 3 pages, taken from the Internet at: http://www.eecg.toronto.edu/~ali/ferro/tutorial.html .	
	CB	"A survey of Circuit Innovations in Ferroelectric Random Access Memories", ALI SHEIKHOESLAMI and P. GLENN GULAK, Proceedings of the IEEE, Vol. 88, No. 5, May, 2000, pp. 667-689.	
	CC	"Generic CVD Reactor", CVD Basics, DANIEL M. DOBKIN, Dec. 7, 2001, 3 pages, taken from the Internet at: http://www.batnet.com/enigmatics/semiconductor_processing/CVD_Fundamentals/introdu...	
✓	CD	"Physical Vapor Deposition", Cougar Labs, Inc., Dec. 7, 2001, 9 pages, taken from the Internet at: http://www.cougarlabs.com/pvd1.html .	

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				First Named Inventor	Udayakumar et al.
				Group Art Unit	2811
				Examiner Name	H. Vu
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✓		"Parasitic Channel Induced by Spin-On-Glass in a Double-Level Metallization Complimentary Metal Oxide Semiconductor Process", M. MURATA, K. YOMAUCHI, H. KOJIMA, A. YOKOYAMA, T. INOUE and T. IWAMORI, published in the Journal of Electrochemical Society, Volume 149, No. 8, 1993, pgs. 2346-2356.	
		"Effects of Oxygen Content on Properties of Silicon Oxide Films Prepared at Room Temperature by Sputtering-Type Electron Cyclotron Resonance Plasma", KATSUHIKO FURUKAWA, YICHUN LIU, HIROSHI NAKASHIMA, DAWEI GAO, YASUHIRO KASHIWAZAKI, KIICHIRO UCHINO, KATSUNORI MURAOKA and HIROHISA TSUZUKI, Journal of Applied Physics, Volume 84, Number 8, October 15, 1998, pp. 4579-4584.	
		Notes taken at the International Symposium on Applications of Ferroelectrics Conference in Nara, Japan in May, 2002. The speaker was H. Nagel of Infineon Technologies and Toshiba Corporation, Key Technologies for High Density FeRAM Application, one page.	
		"The Hydrogen Content of Plasma-Deposited silicon Nitride", W. A. LANFORD and M. J. RAND, American Institute of Physics, J. Appl. Phys. 49(4), April, 1978, Pgs. 2473-2477.	
		"Free Energy Model for the Analysis of Bonding in a-Si ₃ N ₄ H ₂ Alloys", Z. YIN and W. SMITH, J. Vac. Sci. Technol. A, Volume 9, No. 3, May/June, 1991, pg. 972.	
	CG	"Comparison Between HCP CVD and PECVD Silicon Nitride for Advanced Interconnect Applications", J. YOTA, M. JANANI, L.E. CAMILLETTI, A. KAR-ROY, Q.Z. LIU, C. NGUYEN, M.D. WOO J. HANDER, and P. VAN CLEEMPUT, IEEE, 2000, pgs. 76-78.	
✓	CH	"Hydrogen Role on the Properties of Amorphous Silicon Nitride", F. DE BRITO MOTS, J.F. JUSTO and A. FAZZIO, Journal of Applied Physics, Volume 86, Number 4, August 15, 1999, pgs. 1843-1847.	

Examiner Signature	HUNG VU	Date Considered	04/07/05
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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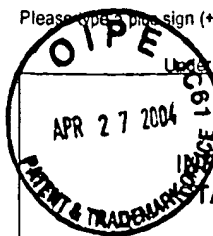


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Substitute for Form 1449A/PTO
**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

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Sheet	1	of	1	Attorney Docket No.	TI-36447
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✓	AA	5,825,068		Yang	10/20/1998	Entire Document
✓	AB	6,642,100	B2	Yang et al.	11/04/2003	Entire Document
	AC					
	AD					
	AF					
	AG					

FOREIGN PATENT DOCUMENTS

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	BB							
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	CA		
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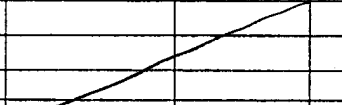
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		Examiner Name	H. Ju	
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		Number	Kind Code ² (if known)			
<input checked="" type="checkbox"/>	AA	6,706,540	B2	Hikosaka et al.	03/16/2004	Entire Document
<input checked="" type="checkbox"/>	AB	6,781,184	B2	Solayappan et al.	08/24/2004	Entire Document
	AC					
	AD					
	AE					
	AF					

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